

Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, Ca 90638 Phone: (562) 404-4474 * Fax: (562) 404-1773 ssdi@ssdi-power.com * www.ssdi-power.com

SDR3A and SDR3ASMS thru SDR3N and SDR3NSMS

3.0 AMPS 50 — 1200 VOLTS 50 — 80 nsec ULTRA FAST RECTIFIER

Designer's Data Sheet

Part Number/Ordering Information $^{1/2}$

SDR3

L Screening 2/

 $\frac{}{TX} = \text{Not Screened}$ $\frac{}{TX} = TX \text{ Level}$

TXV = TXV

S = S Level

L Package Type

__ = Axial Leaded

SMS = Surface Mount Square Tab

Family A = 50 V

A = 50 VB = 100 V

J = 600V K = 800V

D = 200V

M = 1000V

G = 400V

N = 1200V

FEATURES:

Ultra Fast Recovery: 50-80 ns Max @ 25°C 4/ 85-125 ns Max @ 100°C 4/

- Single Chip Construction
- PIV to 1200 Volts
- Low Reverse Leakage Current
- Hermetically Sealed
- For High Efficiency Applications
- Available in Axial and Surface Mount Versions
- Metallurgically Bonded
- TX, TXV, and S-Level Screening Available 2/

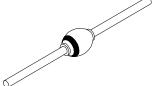
RATING		SYMBOL	VALUE	UNIT
Peak Repetitive Reverse Voltage And DC Blocking Voltage	SDR3A and SDR3ASMS SDR3B and SDR3BSMS SDR3D and SDR3DSMS SDR3G and SDR3GSMS SDR3J and SDR3JSMS SDR3K and SDR3KSMS SDR3M and SDR3MSMS SDR3M and SDR3NSMS	$egin{array}{c} V_{RRM} \ V_{RWM} \ V_{R} \end{array}$	50 100 200 400 600 800 1000 1200	Volts
Rectified Forward Forward Current (Resistive Load, 60 Hz, Sine Wave, $T_A = 25$ °C)		I_0	3	Amp
Peak Surge Current (8.3 msec Pulse, Half Sine Wave Superimposed on Io, allow junction to reach equilibrium between pulses, $T_A = 25$ °C)		$I_{ m FSM}$	75	Amps
Operating & Storage Temperature		T _{OP} and T _{STG}	-65 to +175	°C
Thermal Resistance, Junction to Lead, L = 3/8" Junction to End Tab		$R_{ heta JL} \ R_{ heta JE}$	20 14	°C/W

NOTES:

1/ For Ordering Information, Price, and Availability- Contact Factory.

- 2/ Screening Based on MIL-PRF-19500. Screening Flows Available on Request.
- 3/ Unless Otherwise Specified, All Electrical Characteristics @25°C.
- $\underline{4}$ / Recovery Conditions: $I_F = 0.5$ Amp, $I_R = 1.0$ Amp, I_{RR} to .25 Amp.
- 5/ For information on operating curves, contact factory.

Axial Leaded



SMS



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: RU0013G

DOC



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ELECTRICAL CHARACTERISTICS 3/			ı	
CHARACTERISTICS		SYMBOL	VALUE	UNIT
Instantaneous Forward Voltage Drop ($I_F = 3Adc, 300-500 \mu s Pulse, T_A = 25$ °C)	SDR3A thru SDR3J SDR3K thru SDR3N	$ m V_{F1}$	1.35 1.90	Vdc
Instantaneous Forward Voltage Drop $(I_F = 3Adc, 300-500 \mu s Pulse, T_A = -55^{\circ}C)$	SDR3A thru SDR3J SDR3K thru SDR3N	$ m V_{F2}$	1.50 2.10	Vdc
Maximum Reverse Leakage Current (Rated V_R , 300 μ s Pulse Minimum , $T_A = 25$ °C)		I_{R1}	5	μΑ
Maximum Reverse Leakage Current (Rated V_R , 300 μ s Pulse Minimum , T_A = 100°C)		I_{R2}	500	μΑ
Junction Capacitance (VR = 10 Vdc, $T_A = 25$ °C, $f = 1$ MHz)		$C_{ m J}$	50	pf
Maximum Reverse Recovery Time 4/	SDR3A thru SDR3J SDR3K SDR3M SDR3N	t _{rr}	50 60 70 80	ns

